

OT408 1 A Four-quadrant triac, high surge capability Rev. 01 — 30 July 2008

Product data sheet

Product profile

1.1 General description

Passivated sensitive gate triac in a SOT223 surface-mountable plastic package

1.2 Features

- Sensitive gate
- Direct interfacing to logic level ICs
- High surge capability

- Gate triggering in four quadrants
- Direct interfacing to low power gate drive circuits
- High blocking voltage of 800 V

1.3 Applications

- Home appliances
- Small lamp control

- Low power motor control
- Low power loads in industrial process control

1.4 Quick reference data

- $V_{DRM} \le 800 \text{ V}$
- $I_{TSM} \le 12.5 \text{ A (t = 20 ms)}$
- I_{T(RMS)} ≤ 1 A

- $\blacksquare \quad I_{GT} \leq 5 \ mA$
- $I_{GT} \le 7 \text{ mA } (T2-G+)$

Pinning information

Table 1. **Pinning**

Pin	Description	Simplified outline	Graphic symbol
1	main terminal 1 (T1)		N 1
2	main terminal 2 (T2)	4	T2T1
3	gate (G)		`G sym051
4	mounting base; main terminal 2 (T2)		
		SOT223	



1 A Four-quadrant triac, high surge capability

3. Ordering information

Table 2. Ordering information

Type number	Package	Package						
	Name	Description	Version					
OT408	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223					

4. Limiting values

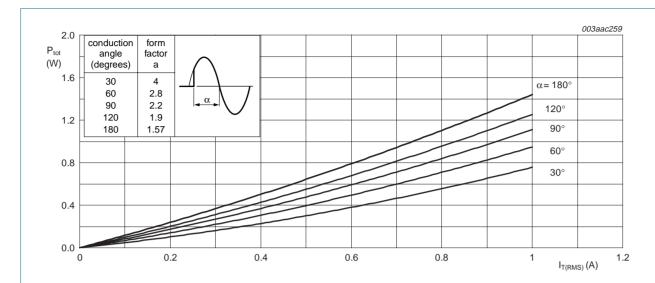
Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
V_{RRM}	repetitive peak reverse voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 103 ^{\circ}\text{C}$; see Figure 4 and 5	-	1	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_j = 25$ °C prior to surge; see Figure 2 and 3			
		t = 20 ms	-	12.5	А
		t = 16.7 ms	-	13.8	А
l ² t	I ² t for fusing	t _p = 10 ms	-	0.78	A ² s
dI _T /dt	rate of rise of on-state current	$I_{TM} = 1 \text{ A}; I_G = 20 \text{ mA};$ $dI_G/dt = 0.2 \text{ A}/\mu\text{s}$			
		T2+ G+	-	50	A/μs
		T2+ G-	-	50	A/μs
		T2- G-	-	50	A/μs
		T2- G+	-	10	A/μs
I_{GM}	peak gate current		-	1	Α
P_GM	peak gate power		-	2	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	+150	°C
T _j	junction temperature		-	125	°C

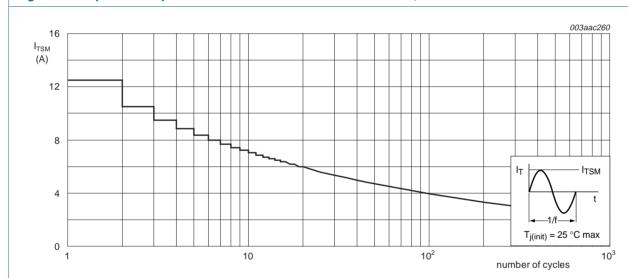
1 A Four-quadrant triac, high surge capability

3 of 13



 α = conduction angle

Fig 1. Total power dissipation as a function of RMS on-state current; maximum values

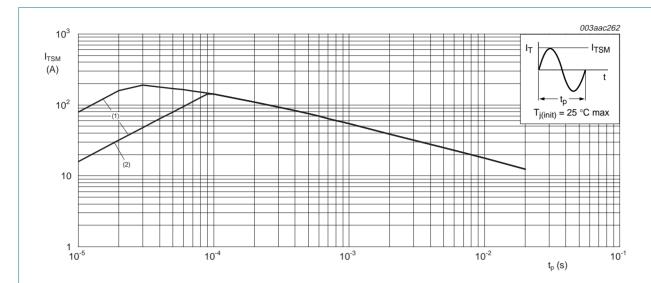


f = 50 Hz

Product data sheet

Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

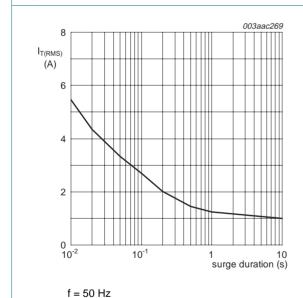
1 A Four-quadrant triac, high surge capability



 $t_{\text{D}} \leq 20 \text{ ms}$

- (1) dl_T/dt limit
- (2) T2- G+ quadrant limit

Fig 3. Non-repetitive peak on-state current as a function of pulse width; maximum values



T_{sp} = 103 °C

Fig 4. RMS on-state current as a function of surge duration; maximum values

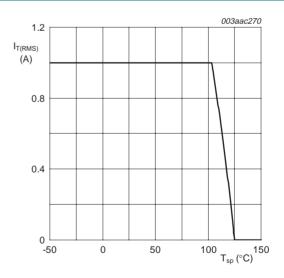


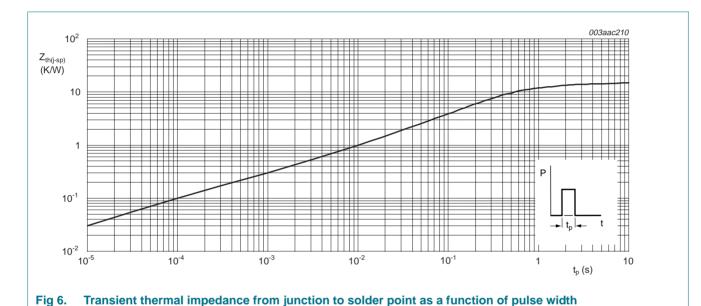
Fig 5. RMS on-state current as a function of solder point temperature; maximum values

1 A Four-quadrant triac, high surge capability

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	full cycle; see Figure 6	-	-	15	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	full cycle				
		for minimum footprint see Figure 13	-	156	-	K/W
		for pad area see <u>Figure 14</u>	-	70	-	K/W



1 A Four-quadrant triac, high surge capability

6. Static characteristics

Table 5. Static characteristics

 $T_i = 25 \,^{\circ}$ C unless otherwise specified.

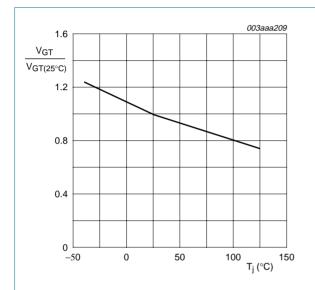
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; see } \frac{\text{Figure 8}}{}$				
		T2+ G+	-	-	5	mA
		T2+ G-	-	-	5	mA
		T2- G-	-	-	5	mA
		T2- G+	-	-	7	mA
I _L latching current		V _D = 12 V; I _G = 0.1 A; see <u>Figure 10</u>				
		T2+ G+	-	-	10	mA
		T2+ G-	-	-	20	mA
		T2- G-	-	-	10	mA
		T2- G+	-	-	10	mA
I _H	holding current	$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; see } \frac{\text{Figure } 11}{}$	-	-	10	mA
V_{T}	on-state voltage	I _T = 1 A; see <u>Figure 9</u>	-	1.3	1.6	V
V_{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; see <u>Figure 7</u>	-	-	1.3	V
		$V_D = V_{DRM}; I_T = 0.1 A; T_j = 125 °C$	0.2	-	-	V
I_D	off-state current	$V_D = V_{DRM(max)}$; $T_j = 125 ^{\circ}C$	-	-	0.5	mA

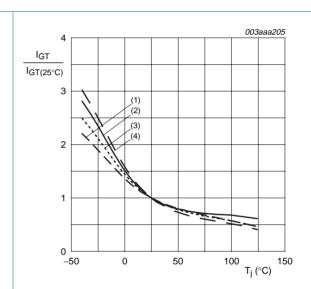
1 A Four-quadrant triac, high surge capability

7. Dynamic characteristics

Table 6. Dynamic characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
dV _D /dt	rate of rise of off-state voltage	$V_{DM} = 0.67 V_{DRM(max)}$; $T_j = 110 ^{\circ}C$; exponential waveform; gate open circuit	20	-	-	V/μs
dV _{com} /dt	rate of change of commutating voltage	$V_{DM} = 400 \text{ V}; T_j = 110 ^{\circ}\text{C}; I_{TM} = 1 \text{ A};$ $dI_{com}/dt = 0.44 \text{ A/ms}$	1	-	-	V/μs



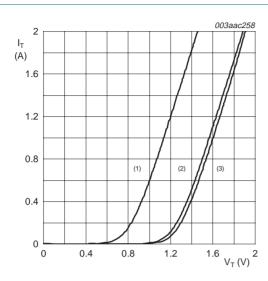


- (1) T2+ G+
- (2) T2+ G-
- (3) T2- G-
- (4) T2- G+

Fig 7. Normalized gate trigger voltage as a function of junction temperature

Fig 8. Normalized gate trigger current as a function of junction temperature

1 A Four-quadrant triac, high surge capability



 $V_0 = 1.254 \text{ V}; R_s = 0.31 \Omega$

- (1) $T_i = 125 \,^{\circ}\text{C}$; typical values
- (2) $T_i = 125 \,^{\circ}\text{C}$; maximum values
- (3) $T_i = 25$ °C; maximum values

Fig 9. On-state current as a function of on-state voltage

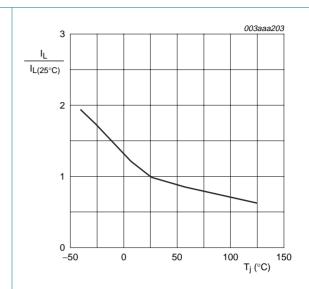


Fig 10. Normalized latching current as a function of junction temperature

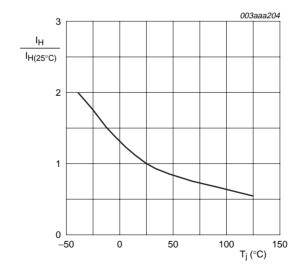


Fig 11. Normalized holding current as a function of junction temperature

SOT223

8. Package outline

Plastic surface-mounted package with increased heatsink; 4 leads

DIMENSIONS (mm are the original dimensions)

ŀ	UNIT	A	A ₁	bp	b ₁	С	D	E	е	e ₁	HE	L _p	Q	v	w	у
	mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT223			SC-73		04-11-10 06-03-16

scale

4 mm

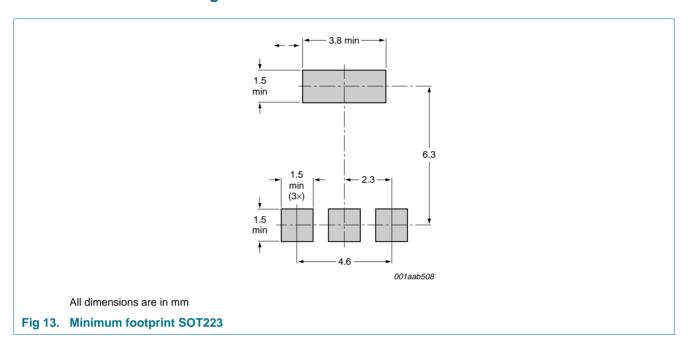
Fig 12. Package outline SOT223 (SC-73)

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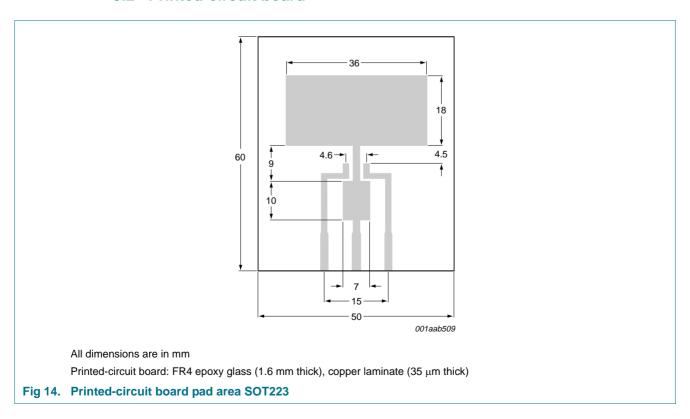
1 A Four-quadrant triac, high surge capability

9. Mounting

9.1 Mounting instructions



9.2 Printed-circuit board



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1 A Four-quadrant triac, high surge capability

10. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
OT408_1	20080730	Product data sheet	-	-

1 A Four-quadrant triac, high surge capability

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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1 A Four-quadrant triac, high surge capability

13. Contents

1	Product profile 1
1.1	General description 1
1.2	Features
1.3	Applications
1.4	Quick reference data 1
2	Pinning information 1
3	Ordering information 2
4	Limiting values 2
5	Thermal characteristics 5
6	Static characteristics 6
7	Dynamic characteristics
8	Package outline 9
9	Mounting 10
9.1	Mounting instructions
9.2	Printed-circuit board
10	Revision history
11	Legal information 12
11.1	Data sheet status
11.2	Definitions
11.3	Disclaimers
11.4	Trademarks12
12	Contact information 12
13	Contents

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